

TOSHIBA Transistor Silicon NPN/PNP Epitaxial Type
(PCT Process) (Transistor with Built-in Bias Resistor)

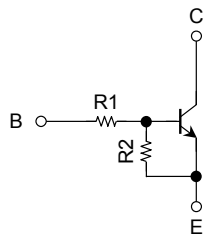
RN4982AFS

Switching, Inverter Circuit, Interface Circuit and
Driver Circuit Applications

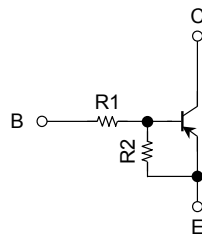
- Two devices are incorporated into a fine-pitch, small-mold (6-pin) package.
- Incorporating a bias resistor into the transistor reduces the number of parts, so enabling the manufacture of ever more compact equipment and lowering assembly cost.
- Lead (Pb) - free

Equivalent Circuit and Bias Resistor Values

Q1



Q2

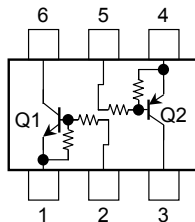


R1: 10 kΩ

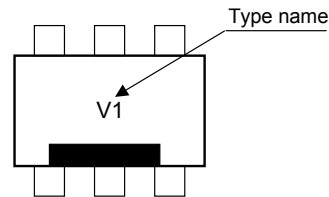
R2: 10 kΩ

(Q1, Q2 common)

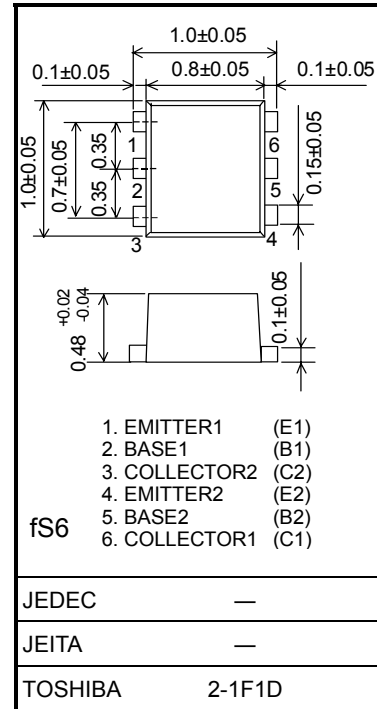
Equivalent Circuit (top view)



Marking



Unit: mm



Weight: 0.001 g (typ.)

Maximum Ratings (Ta = 25°C) (Q1)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	10	V
Collector current	I_C	80	mA

Maximum Ratings (Ta = 25°C) (Q2)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-10	V
Collector current	I_C	-80	mA

Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristic	Symbol	Rating	Unit
Collector power dissipation	P_C (Note)	50	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Note: Total rating

Electrical Characteristics (Ta = 25°C) (Q1)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 50\text{ V}, I_E = 0$	—	—	100	nA
	I_{CEO}	$V_{CE} = 50\text{ V}, I_B = 0$	—	—	500	
Emitter cutoff current	I_{EBO}	$V_{EB} = 10\text{ V}, I_C = 0$	0.41	—	0.63	mA
DC current gain	h_{FE}	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}$	50	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5\text{ mA}, I_B = 0.25\text{ mA}$	—	—	0.15	V
Input voltage (ON)	$V_{I(ON)}$	$V_{CE} = 0.2\text{ V}, I_C = 5\text{ mA}$	1.2	—	2.6	V
Input voltage (OFF)	$V_{I(OFF)}$	$V_{CE} = 5\text{ V}, I_C = 0.1\text{ mA}$	0.8	—	1.5	V
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	0.7	—	pF

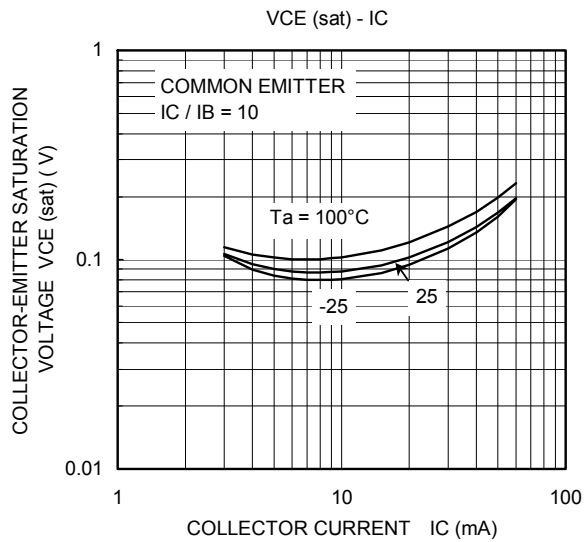
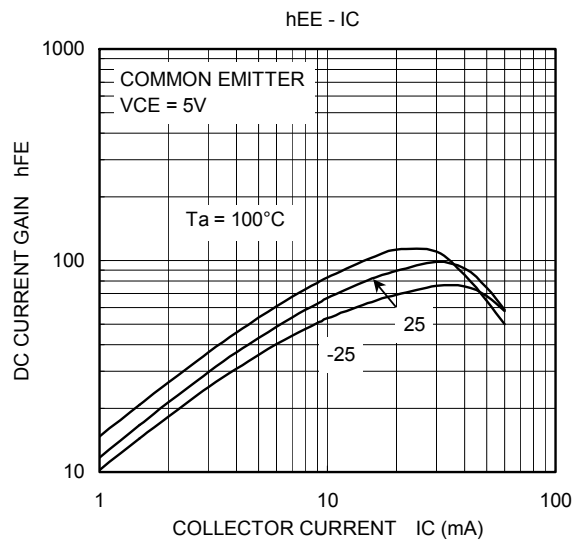
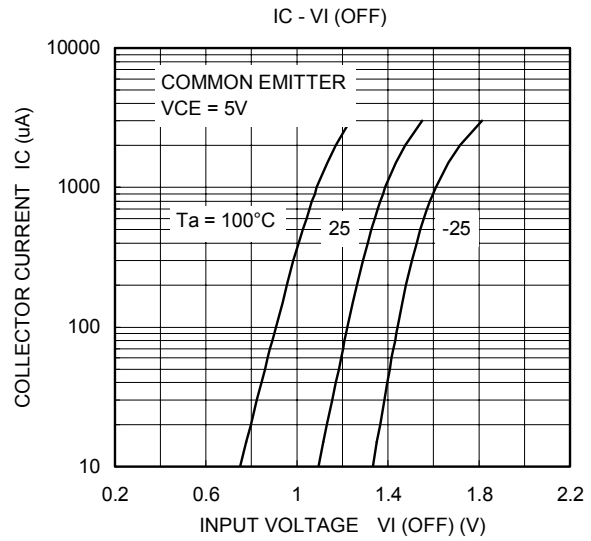
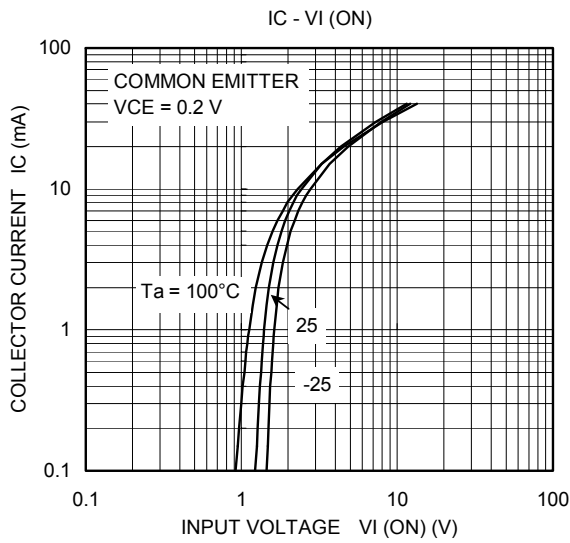
Electrical Characteristics (Ta =25°C) (Q2)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
	I_{CEO}	$V_{CE} = -50\text{ V}, I_B = 0$	—	—	-500	
Emitter cutoff current	I_{EBO}	$V_{EB} = -10\text{ V}, I_C = 0$	-0.41	—	-0.63	mA
DC current gain	h_{FE}	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	50	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	—	-0.15	V
Input voltage (ON)	$V_{I(ON)}$	$V_{CE} = -0.2\text{ V}, I_C = -5\text{ mA}$	-1.2	—	-2.6	V
Input voltage (OFF)	$V_{I(OFF)}$	$V_{CE} = -5\text{ V}, I_C = -0.1\text{ mA}$	-0.8	—	-1.5	V
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	0.9	—	pF

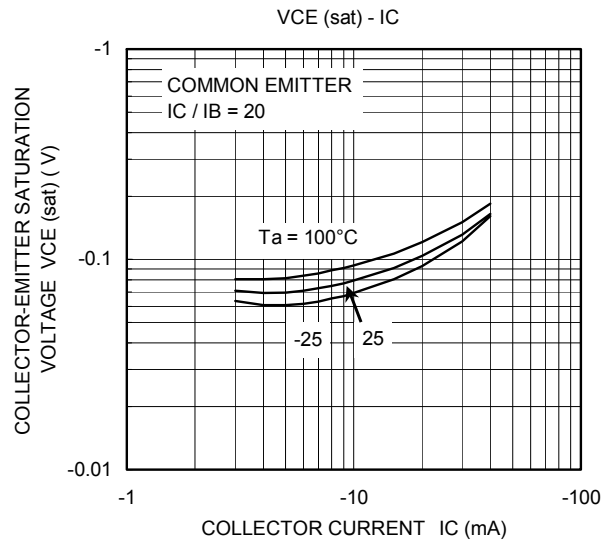
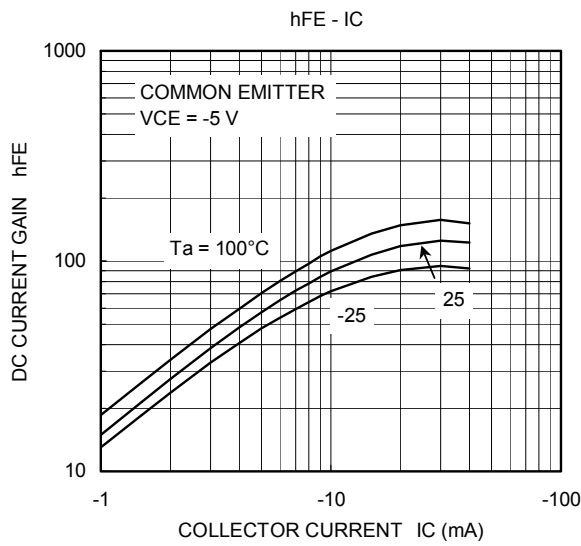
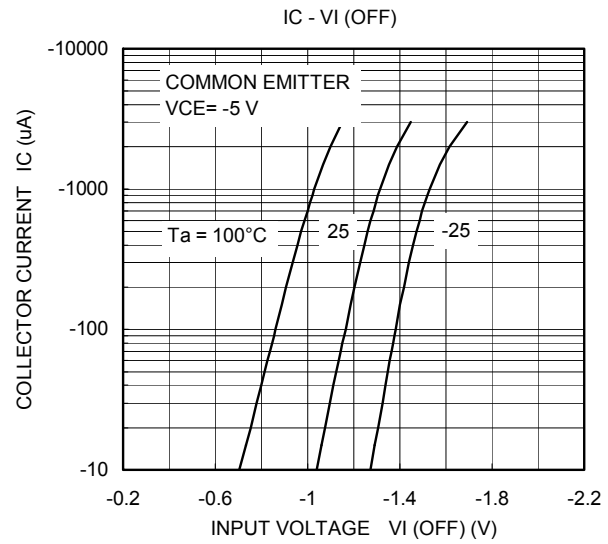
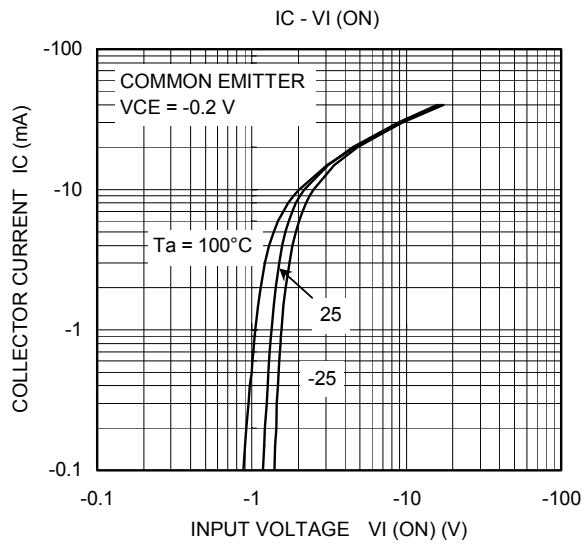
Electrical Characteristics (Ta =25°C) (Q1, Q2 common)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Input resistor	R1	—	8	10	12	kΩ
Resistor ratio	R1/R2	—	0.8	1.0	1.2	

Q1



Q2



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